

XR8051, XR8052, XR8054

Low Cost, High Speed Rail-to-Rail Amplifiers

FEATURES

- 175MHz bandwidth
- Fully specified at +3V, +5V and +/-5V supplies
- Output voltage range:
0.03V to 4.95V; $V_S = +5$; $R_L = 2k\Omega$
- Input voltage range:
-0.3V to +4.1V; $V_S = +5$
- 190V/ μ s slew rate
- 2.6mA supply current per amplifier
- ± 100 mA linear output current
- ± 125 mA short circuit current
- XR8051 directly replaces AD8051, AD8091
- XR8052 directly replaces AD8052, AD8092
- XR8054 directly replaces AD8054

APPLICATIONS

- Video driver
- Video surveillance and distribution
- A/D driver
- Active filters
- CCD imaging systems
- CD/DVD ROM
- Coaxial cable drivers
- High capacitive load driver
- Portable/battery-powered applications
- Twisted pair driver
- Telecom and optical terminals

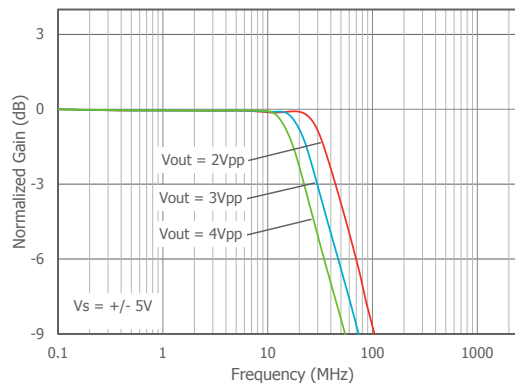
General Description

The XR8051 (single), XR8052 (dual) and XR8054(quad) are low cost, voltage feedback amplifiers. These amplifiers are designed to operate on +3V to +5V, or ± 5 V supplies. The input voltage range extends 300mV below the negative rail and 0.9V below the positive rail.

The XR8051, XR8052, and XR8054 offer superior dynamic performance with a 175MHz small signal bandwidth and 190V/ μ s slew rate. The combination of low power, high output current drive, and rail-to-rail performance make these amplifiers well suited for battery-powered systems and video applications.

The combination of low cost and high performance make the XR8051, XR8052, and XR8054 suitable for high volume applications in both consumer and industrial applications such as video surveillance and distribution systems, professional and IPC cameras, active filter circuits, coaxial cable drivers, and electronic white boards.

Large Signal Frequency Response at +/-5V



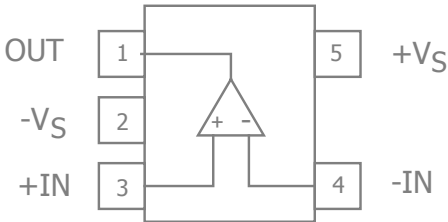
Ordering Information

Part Number	Package	MSL Rating	Pb-Free	RoHS Compliant	Operating Temperature	Packaging Method
XR8051ASO8X	SOIC-8	MSL-2	Yes	Yes	-40°C to +125°C	Reel
XR8051AST5X	TSOT-5	MSL-1	Yes	Yes	-40°C to +125°C	Reel
XR8052ASO8X	SOIC-8	MSL-2	Yes	Yes	-40°C to +125°C	Reel
XR8052AMP8X	MSOP-8	MSL-1	Yes	Yes	-40°C to +125°C	Reel
XR8054ASO14X	SOIC-14	MSL-2	Yes	Yes	-40°C to +125°C	Reel
XR8054ATP14X	TSSOP-14	MSL-1	Yes	Yes	-40°C to +125°C	Reel

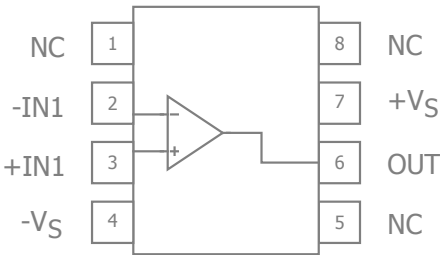


XR8051 Pin Configurations

TSOT-5

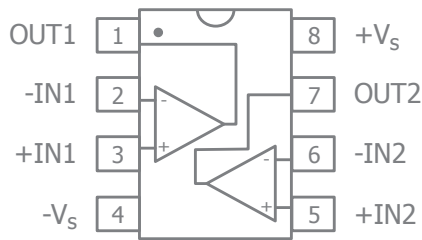


SOIC-8



XR8052 Pin Configuration

SOIC-8 / MSOP-8



XR8051 Pin Assignments

TSOT-5

Pin No.	Pin Name	Description
1	OUT	Output
2	-VS	Negative supply
3	+IN	Positive input
4	-IN	Negative input
5	+VS	Positive supply

SOIC-8

Pin No.	Pin Name	Description
1	NC	No Connect
2	-IN	Negative input
3	+IN	Positive input
4	-VS	Negative supply
5	NC	No Connect
6	OUT	Negative input
7	+VS	Positive supply
8	NC	No Connect

XR8052 Pin Assignments

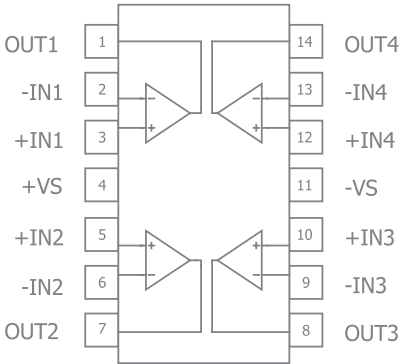
SOIC-8 / MSOP-8

Pin No.	Pin Name	Description
1	OUT1	Output, channel 1
2	-IN1	Negative input, channel 1
3	+IN1	Positive input, channel 1
4	-VS	Negative supply
5	+IN2	Positive input, channel 2
6	-IN2	Negative input, channel 2
7	OUT2	Output, channel 2
8	+VS	Positive supply



XR8054 Pin Configuration

SOIC/TSSOP



XR8054 Pin Assignments

SOIC/TSSOP

Pin No.	Pin Name	Description
1	OUT1	Output, channel 1
2	-IN1	Negative input, channel 1
3	+IN1	Positive input, channel 1
4	+VS	Positive supply
5	+IN2	Positive input, channel 2
6	-IN2	Negative input, channel 2
7	OUT2	Output, channel 2
8	OUT3	Output, channel 3
9	-IN3	Negative input, channel 3
10	+IN3	Positive input, channel 3
11	-VS	Negative supply
12	+IN4	Positive input, channel 4
13	-IN4	Negative input, channel 4
14	OUT4	Output, channel 4



Absolute Maximum Ratings

The safety of the device is not guaranteed when it is operated above the "Absolute Maximum Ratings". The device should not be operated at these "absolute" limits. Adhere to the "Recommended Operating Conditions" for proper device function. The information contained in the Electrical Characteristics tables and Typical Performance plots reflect the operating conditions noted on the tables and plots.

Parameter	Min	Max	Unit
Supply Voltage	0	+14	V
Input Voltage Range	$-V_S - 0.5V$	$+V_S + 0.5V$	V

Reliability Information

Parameter	Min	Typ	Max	Unit
Junction Temperature			150	°C
Storage Temperature Range	-65		170	°C
Lead Temperature (Soldering, 10s)			260	°C
Package Thermal Resistance				
5-Lead SOT23		221		°C/W
8-Lead MSOP		139		°C/W
8-Lead SOIC		100		°C/W
14-Lead SOIC		88		°C/W
14-Lead TSSOP		96		°C/W

Notes:

Package thermal resistance (θ_{JA}), JEDEC standard, multi-layer test boards, still air.

ESD Protection

Product	SOIC-8
Human Body Model (HBM)	1k
Charged Device Model (CDM)	2k

Recommended Operating Conditions

Parameter	Min	Typ	Max	Unit
Operating Temperature Range	-40		+125	°C
Supply Voltage Range	2.7		12.6	V



Electrical Characteristics at +3V

$T_A = 25^\circ\text{C}$, $R_f = 1.5\text{k}\Omega$, $R_L = 2\text{k}\Omega$ to $V_S/2$, $G = 2$; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Frequency Domain Response						
GBWP	-3dB Gain Bandwidth Product	G = +11, V _{OUT} = 0.2V _{pp}		62		MHz
UGBW	Unity Gain Bandwidth	V _{OUT} = 0.2V _{pp} , R _F = 0		160		MHz
BW _{SS}	-3dB Bandwidth	V _{OUT} = 0.2V _{pp}		60		MHz
f _{0.1dB}	0.1dB gain flatness	V _{OUT} = 0.2V _{pp} , R _L =150Ω		20		MHz
BW _{LS}	Large Signal Bandwidth	V _{OUT} = 2V _{pp}		40		MHz
DG	Differential Gain	DC-coupled Ouput		0.03		%
		AC-coupled Ouput		0.04		%
DP	Differential Phase	DC-coupled Ouput		0.03		°
		AC-coupled Ouput		0.06		°
Time Domain Response						
t _R , t _F	Rise and Fall Time	V _{OUT} = 0.2V step; (10% to 90%)		5		ns
t _S	Settling Time to 0.1%	V _{OUT} = 1V step		25		ns
OS	Overshoot	V _{OUT} = 0.2V step		8		%
SR	Slew Rate	G=-1, 2V step		165		V/μs
Distortion/Noise Response						
THD	Total Harmonic Distortion	1MHz, Vout=1Vpp		75		dBc
e _n	Input Voltage Noise	> 50kHz		16		nV/√Hz
X _{TALK}	Crosstalk	f=5MHz		58		dB
DC Performance						
V _{IO}	Input Offset Voltage			0.5		mV
dV _{IO}	Average Drift			5		μV/°C
I _b	Input Bias Current			1.4		μA
dI _b	Average Drift			2		nA/°C
I _{os}	Input Offset Current			0.05		μA
PSRR	Power Supply Rejection Ratio	DC		102		dB
A _{OL}	Open-Loop Gain	R _L = 2kΩ ⁽²⁾		92		dB
I _S	Supply Current	per channel		2.6		mA
Input Characteristics						
C _{IN}	Input Capacitance			0.5		pF
CMIR	Common Mode Input Range			-0.3 to 2.1		V
CMRR	Common Mode Rejection Ratio	DC , V _{cm} =0V to 1.5V		100		dB
Output Characteristics						
V _{OUT}	Output Voltage Swing	R _L = 150Ω		0.3 to 2.75		V
		R _L = 2kΩ		0.02 to 2.96		V
I _{OUT}	Output Current			±100		mA
I _{SC}	Short-Circuit Output Current	V _{OUT} = V _S / 2		±125		mA
V _S	Power Supply Operatong Range			2.7 to 12		V

Notes:

- 100% tested at 25°C
- Guaranteed by characterization, simulation or statistical analysis



Electrical Characteristics at +5V

$T_A = 25^\circ\text{C}$, $R_f = 1.5\text{k}\Omega$, $R_L = 2\text{k}\Omega$ to $V_S/2$, $G = 2$; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Frequency Domain Response						
GBWP	-3dB Gain Bandwidth Product	G = +11, V _{OUT} = 0.2V _{pp}		64		MHz
UGBW	Unity Gain Bandwidth	V _{OUT} = 0.2V _{pp} , R _F = 0		165		MHz
BW _{SS}	-3dB Bandwidth	V _{OUT} = 0.2V _{pp}		62		MHz
f _{0.1dB}	0.1dB gain flatness	V _{OUT} = 0.2V _{pp} , R _L =150Ω		20		MHz
BW _{LS}	Large Signal Bandwidth	V _{OUT} = 2V _{pp}		45		MHz
DG	Differential Gain	DC-coupled Ouput		0.03		%
		AC-coupled Ouput		0.04		%
DP	Differential Phase	DC-coupled Ouput		0.03		°
		AC-coupled Ouput		0.06		°
Time Domain Response						
t _R , t _F	Rise and Fall Time	V _{OUT} = 0.2V step		5		ns
t _S	Settling Time to 0.1%	V _{OUT} = 2V step		25		ns
OS	Overshoot	V _{OUT} = 0.2V step		5		%
SR	Slew Rate	G=-1 , 4V step,		185		V/μs
Distortion/Noise Response						
THD	Total Harmonic Distortion	1MHz, V _{OUT} =2V _{pp}		-75		dB
e _n	Input Voltage Noise	> 50kHz		16		nV/√Hz
X _{TALK}	Crosstalk	f=5MHz		58		dB
DC Performance						
V _{IO}	Input Offset Voltage ⁽¹⁾		-7	0.5	7	mV
dV _{IO}	Average Drift			5		μV/°C
I _b	Input Bias Current ⁽¹⁾		-2	1.4	2	μA
dI _b	Average Drift			2		nA/°C
I _{os}	Input Offset Current ⁽¹⁾		-0.75	0.05	0.75	μA
PSRR	Power Supply Rejection Ratio ⁽¹⁾	DC	80	102		dB
A _{OL}	Open-Loop Gain	R _L = 2kΩ ⁽²⁾	80	92		dB
I _S	Supply Current ⁽¹⁾	per channel		2.6	4	mA
Input Characteristics						
C _{IN}	Input Capacitance			0.5		pF
CMIR	Common Mode Input Range			-0.3 to 4.1		V
CMRR	Common Mode Rejection Ratio ⁽¹⁾	DC , V _{cm} = 0V to 3.5V	75	100		dB
Output Characteristics						
V _{OUT}	Output Voltage Swing	R _L = 150Ω ⁽¹⁾	4.65	0.1 to 4.9	0.35	V
		R _L = 2kΩ		0.03 to 4.95		V
I _{OUT}	Output Current			±100		mA
I _{SC}	Short-Circuit Output Current	V _{OUT} = V _S / 2		±125		mA
V _S	Power Supply Operationg Range			2.7 to 12		V

Notes:

- 100% tested at 25°C
- Guaranteed by characterization, simulation or statistical analysis



Electrical Characteristics at $\pm 5V$

$T_A = 25^\circ\text{C}$, $R_f = 1.5\text{k}\Omega$, $R_L = 2\text{k}\Omega$ to GND, $G = 2$; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Frequency Domain Response						
GBWP	-3dB Gain Bandwidth Product	G = +11, V _{OUT} = 0.2V _{pp}		65		MHz
UGBW	Unity Gain Bandwidth	V _{OUT} = 0.2V _{pp} , R _F = 0		175		MHz
BW _{SS}	-3dB Bandwidth	V _{OUT} = 0.2V _{pp}		65		MHz
f _{0.1dB}	0.1dB gain flatness	V _{OUT} = 0.2V _{pp} , R _L =150Ω		20		MHz
BW _{LS}	Large Signal Bandwidth	V _{OUT} = 2V _{pp}		50		MHz
DG	Differential Gain	DC-coupled Ouput		0.03		%
		AC-coupled Ouput		0.04		%
DP	Differential Phase	DC-coupled Ouput		0.03		°
		AC-coupled Ouput		0.06		°
Time Domain Response						
t _R , t _F	Rise and Fall Time	V _{OUT} = 0.2V step		5		ns
t _S	Settling Time to 0.1%	V _{OUT} = 2V step, R _L = 100Ω		25		ns
OS	Overshoot	V _{OUT} = 0.2V step		5		%
SR	Slew Rate	G=-1 , 5V step		190		V/μs
Distortion/Noise Response						
THD	Total Harmonic Distortion	1MHz, V _{OUT} =2V _{PP}		76		dBc
e _n	Input Voltage Noise	> 50kHz		16		nV/√Hz
X _{TALK}	Crosstalk	f=5MHz		58		dB
DC Performance						
V _{IO}	Input Offset Voltage			0.5		mV
dV _{IO}	Average Drift			5		μV/°C
I _b	Input Bias Current			1.3		μA
dI _b	Average Drift			2		nA/°C
I _{os}	Input Offset Current			0.04		μA
PSRR	Power Supply Rejection Ratio	DC		102		dB
A _{OL}	Open-Loop Gain	R _L = 2kΩ ⁽²⁾		92		dB
I _S	Supply Current	per channel		2.6		mA
Input Characteristics						
C _{IN}	Input Capacitance			0.5		pF
CMIR	Common Mode Input Range			-5.3 to 4.1		V
CMRR	Common Mode Rejection Ratio ⁽¹⁾	DC , V _{cm} = -5V to 3.5V		100		dB
Output Characteristics						
V _{OUT}	Output Voltage Swing	R _L = 150Ω		-4.8 to 4.8		V
		R _L = 2kΩ		-4.95 to 4.93		V
I _{OUT}	Output Current			+/- 100		mA
I _{SC}	Short-Circuit Output Current	V _{OUT} = V _S / 2		+/-125		mA
V _S	Power Supply Operatong Range			2.7 to 12		V

Notes:

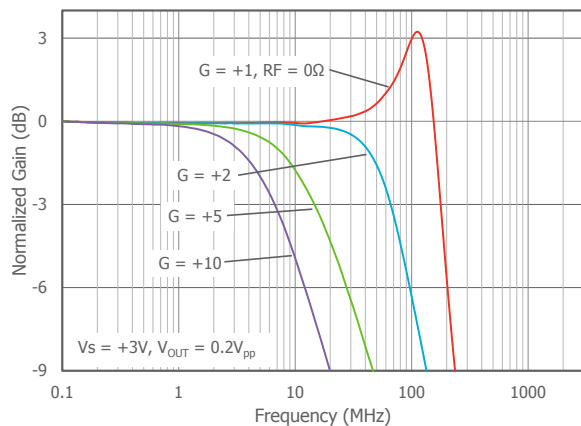
- 100% tested at 25°C
- Guaranteed by characterization, simulation or statistical analysis



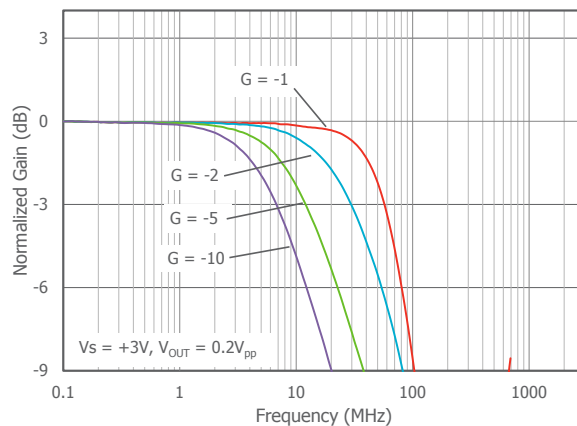
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = +3\text{V}$, $R_L = 2\text{k}\Omega$ to $V_S/2$, $A_V = +2$, $R_F = 1.5\text{k}\Omega$; unless otherwise noted.

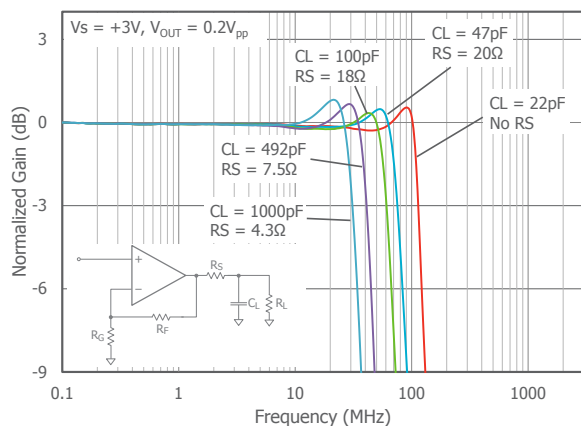
Non-Inverting Freq. Resp.



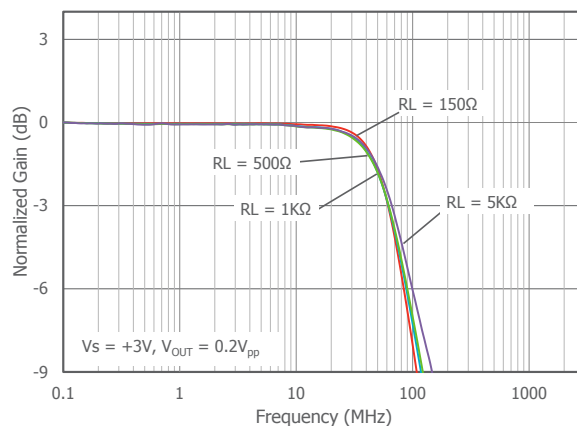
Inverting Freq. Resp.



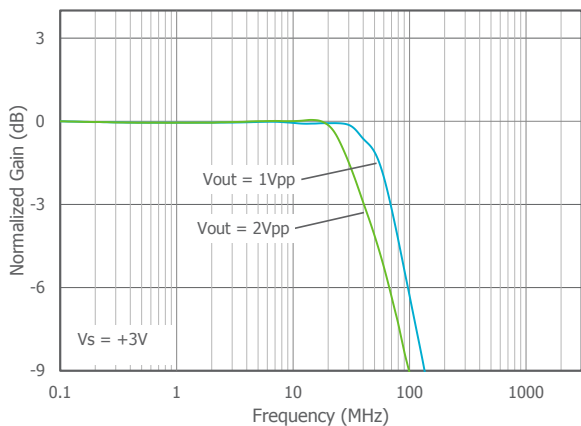
Freq. Resp. vs CL



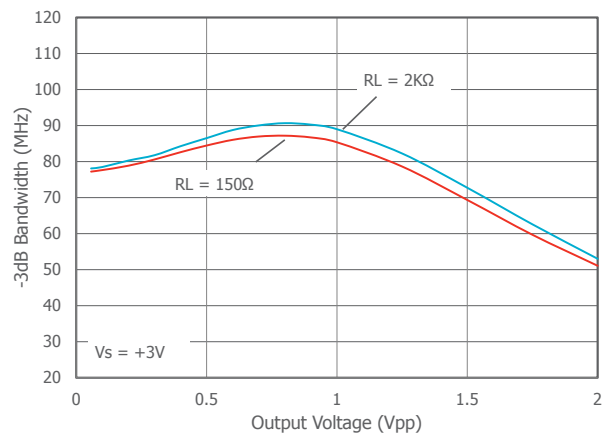
Freq. Resp. vs RL



Large Signal Freq. Resp.



-3dB BW vs Output Voltage

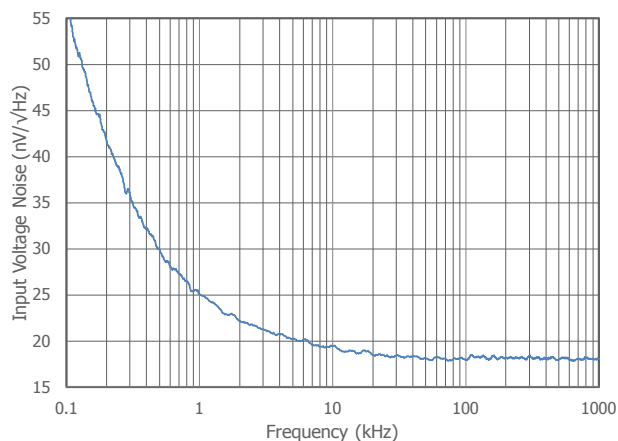




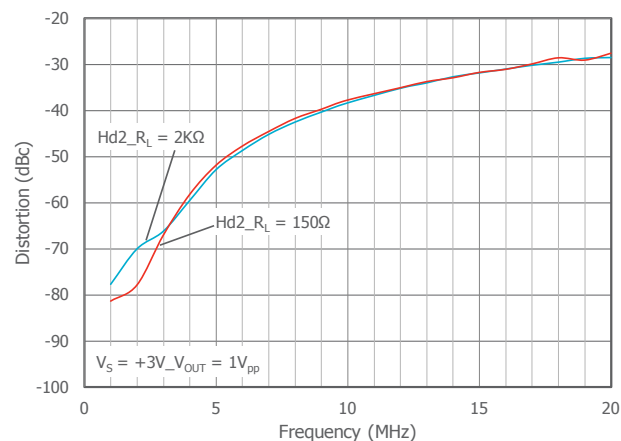
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = +3\text{V}$, $R_L = 2\text{k}\Omega$ to $V_S/2$, $A_V = +2$, $R_F = 1.5\text{k}\Omega$; unless otherwise noted.

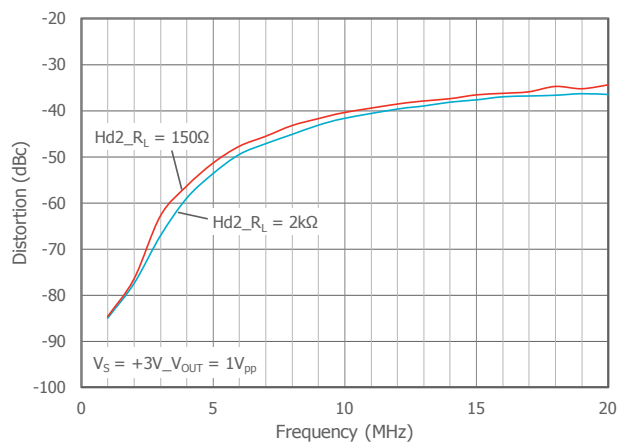
Input Voltage Noise vs Freq.



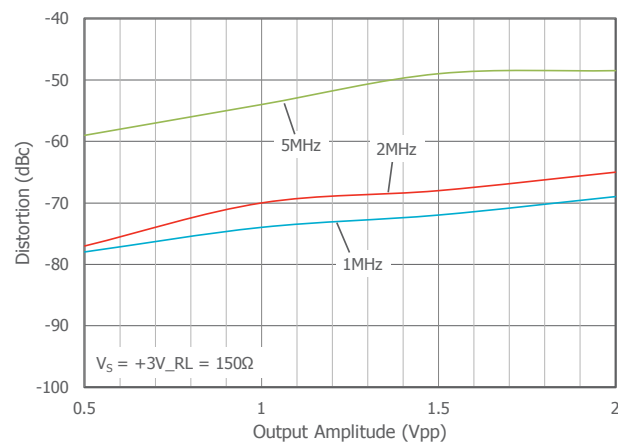
2nd Harmonic Distortion Vs R_L over Freq.



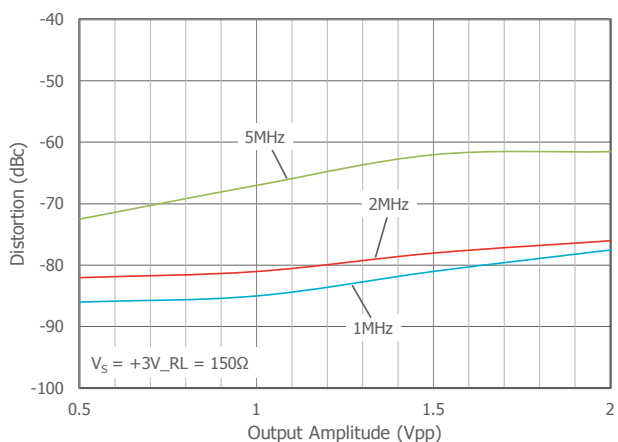
3rd Harmonic Distortion Vs R_L over Freq.



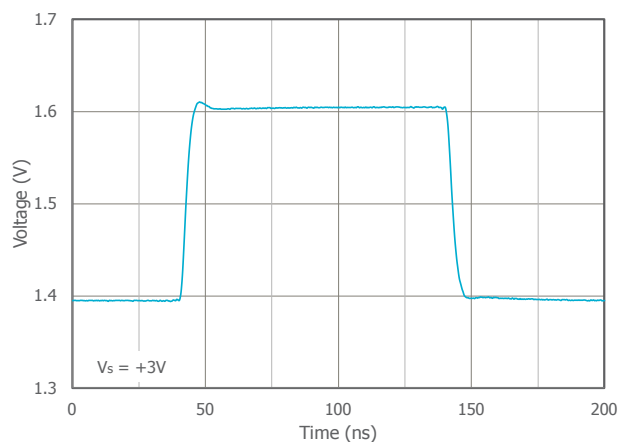
2nd Harmonic Distortion Vs V_o over Freq.



3rd Harmonic Distortion Vs V_o over Freq.



Non-Inverting Small Signal Pulse Response

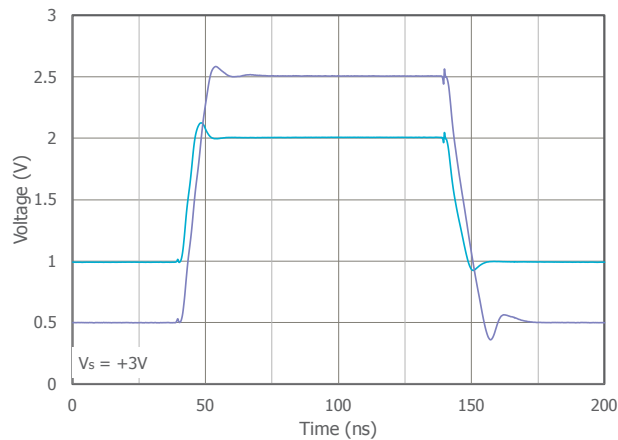




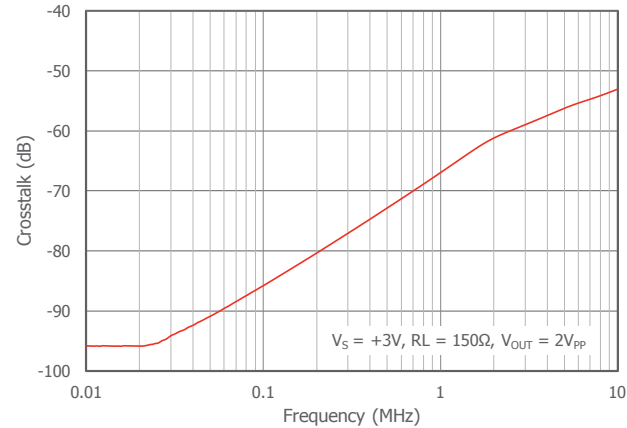
Typical Performance Characteristics

TA = 25°C, VS = +3V, RL = 2kΩ to VS/2, AV=+2, RF=1.5kΩ ; unless otherwise noted.

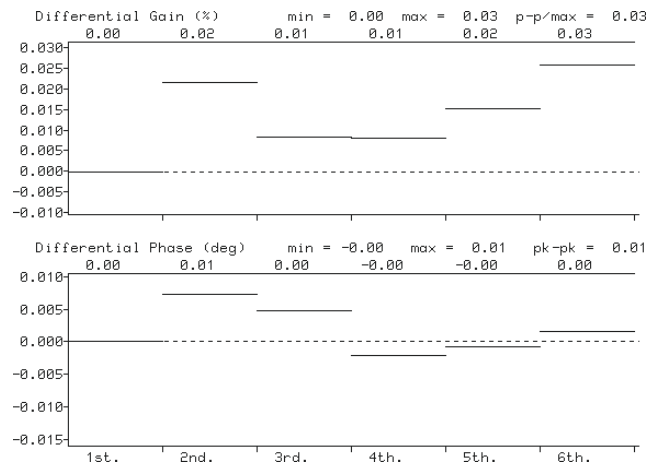
Non-Inverting Large Signal Pulse Response



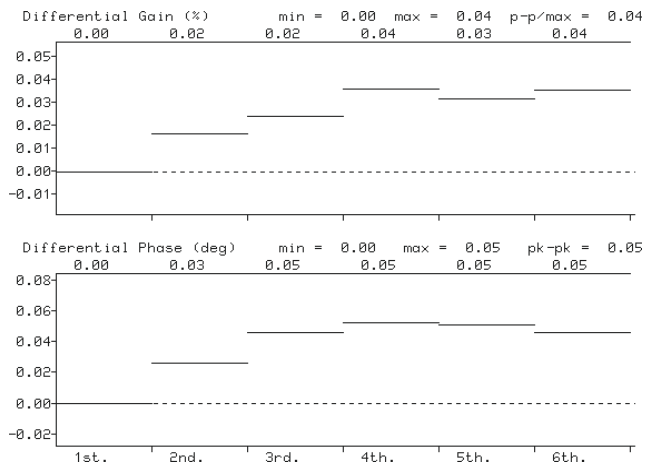
Crosstalk vs Frequency (XR8052)



Differential Gain & Phase_DC Coupled



Differential Gain & Phase_AC Coupled



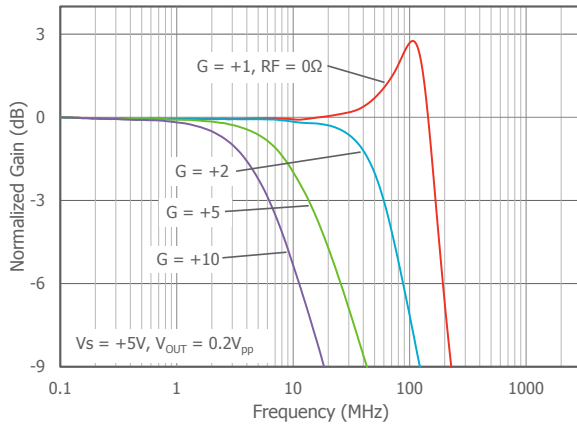
XR8051, XR8052, XR8054 Low Cost, High Speed Rail-to-Rail Amplifiers Rev 1A



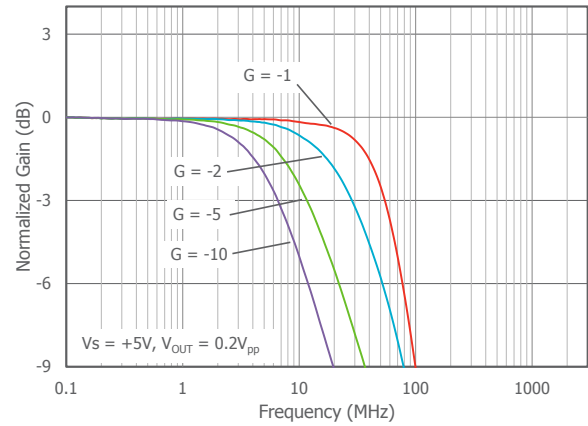
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = +5\text{V}$, $R_L = 2\text{k}\Omega$ to $V_S/2$, $A_V = +2$, $R_F = 1.5\text{k}\Omega$; unless otherwise noted.

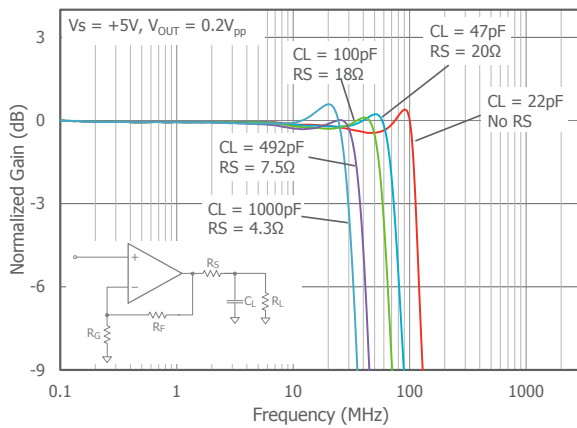
Non-Inverting Freq. Resp.



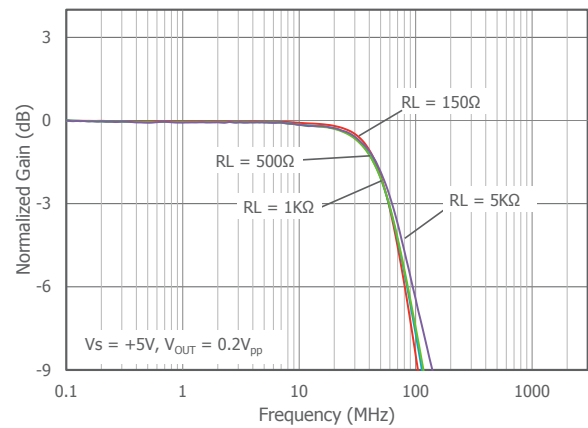
Inverting Freq. Resp.



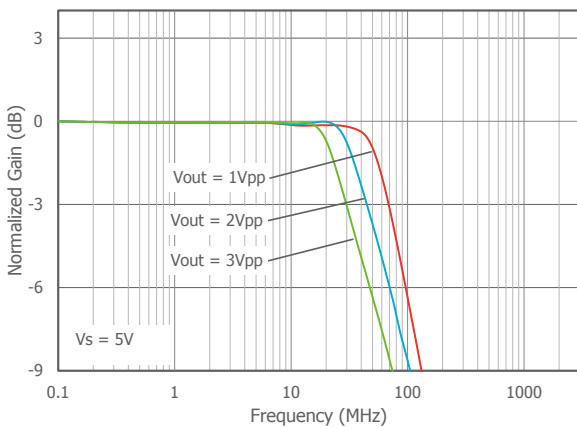
Freq. Resp. vs CL



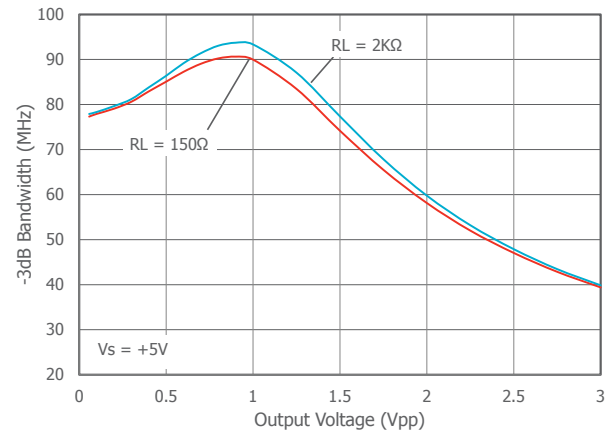
Freq. Resp. vs RL



Large Signal Freq. Resp.



-3dB BW vs Output Voltage

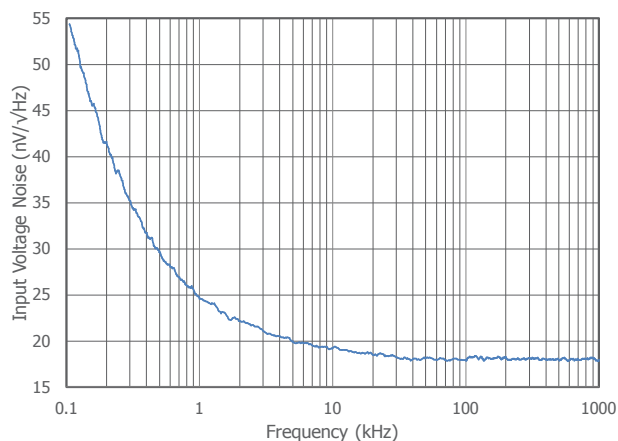




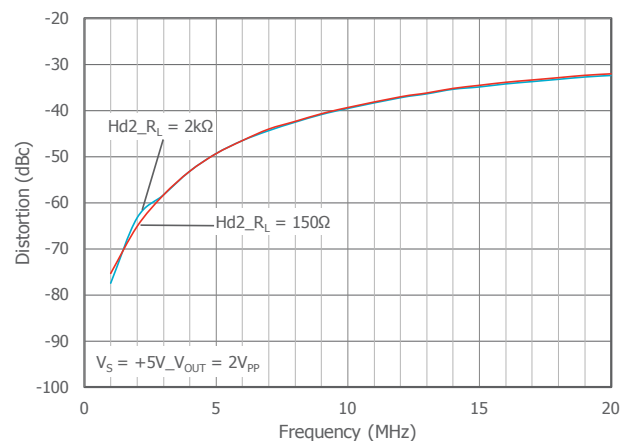
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = +5\text{V}$, $R_L = 2\text{k}\Omega$ to $V_S/2$, $A_V = +2$, $R_F = 1.5\text{k}\Omega$; unless otherwise noted.

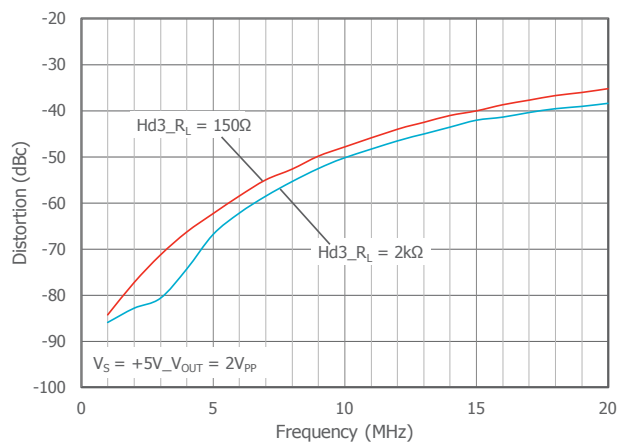
Input Voltage Noise vs Freq.



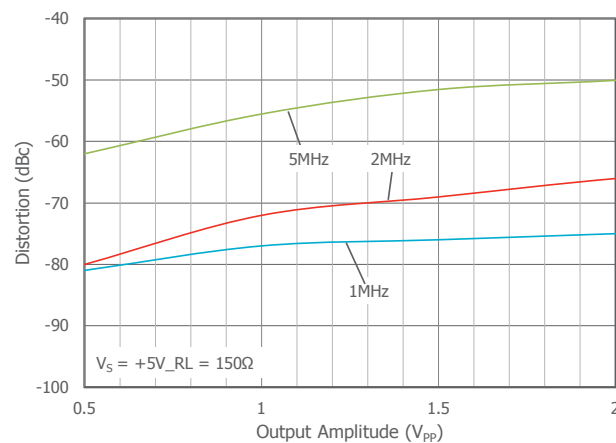
2nd Harmonic Distortion Vs R_L over Freq.



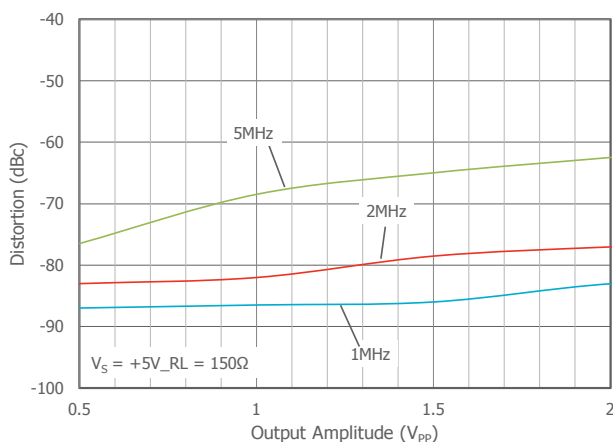
3rd Harmonic Distortion Vs R_L over Freq.



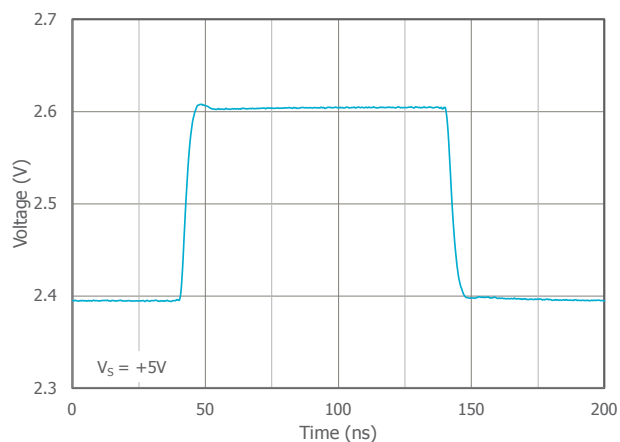
2nd Harmonic Distortion Vs V_o over Freq.



3rd Harmonic Distortion Vs V_o over Freq.



Non-Inverting Small Signal Pulse Response

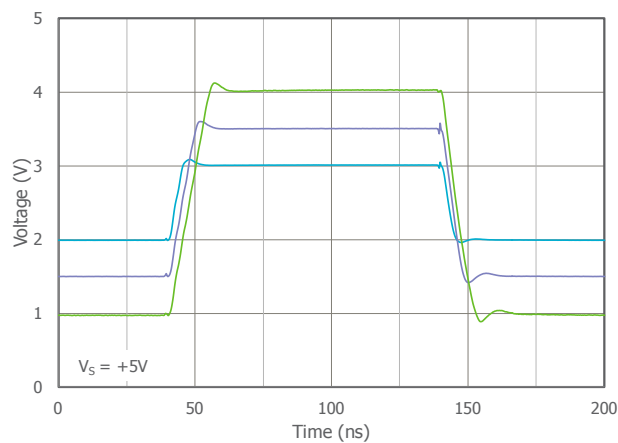




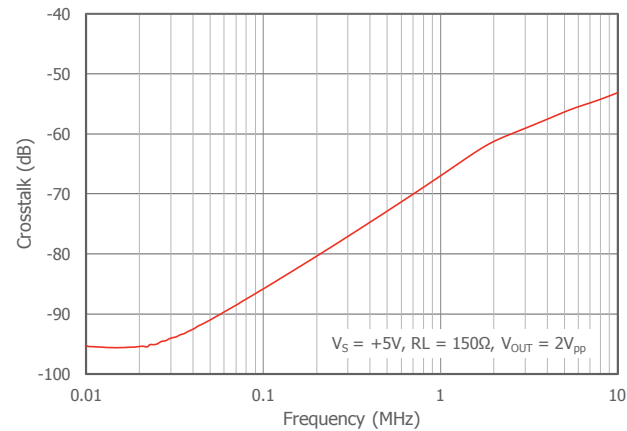
Typical Performance Characteristics

TA = 25°C, VS = +5V, RL = 2kΩ to VS/2, AV=+2, RF=1.5kΩ ; unless otherwise noted.

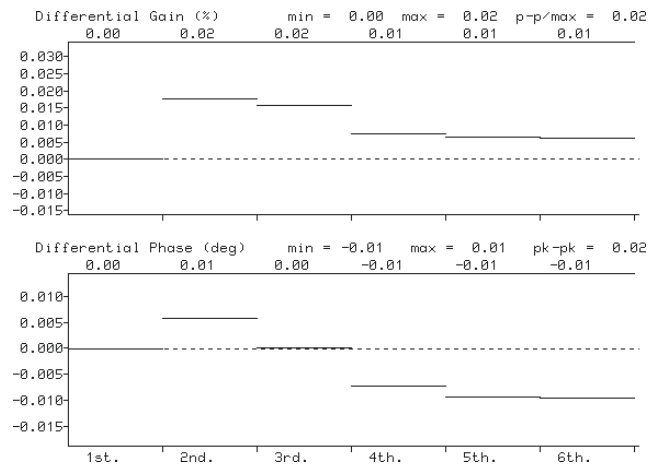
Non-Inverting Large Signal Pulse Response



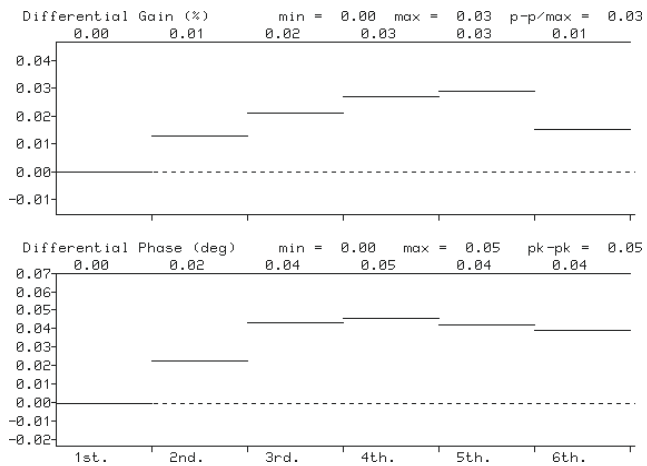
Crosstalk vs Frequency (XR8052)



Differential Gain & Phase_DC Coupled



Differential Gain & Phase_AC Coupled



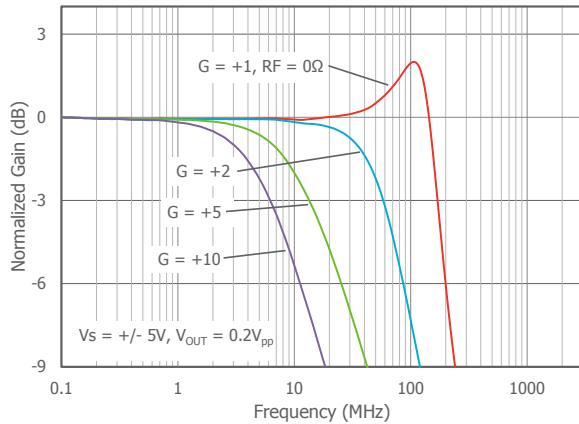
XR8051, XR8052, XR8054 Low Cost, High Speed Rail-to-Rail Amplifiers Rev 1A



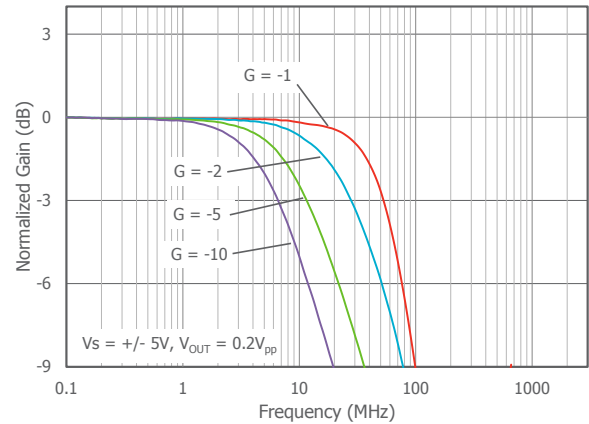
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = \pm 5\text{V}$, $R_L = 2\text{k}\Omega$ to GND, $A_V = +2$, $R_F = 1.5\text{k}\Omega$; unless otherwise noted.

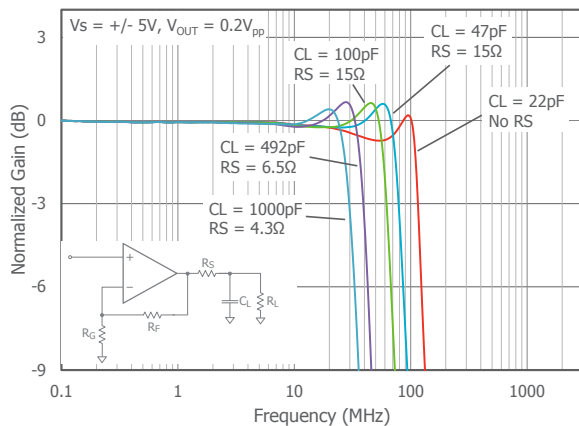
Non-Inverting Freq. Resp.



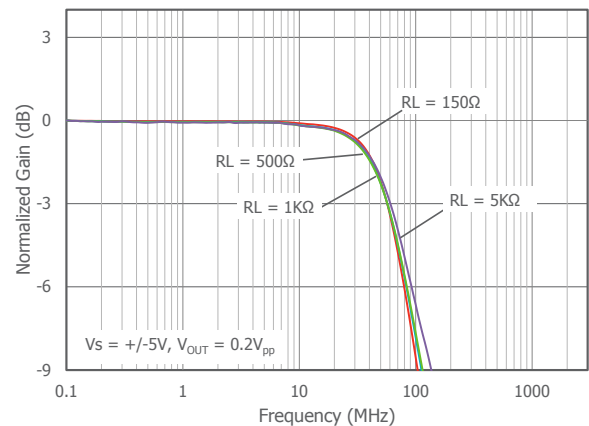
Inverting Freq. Resp.



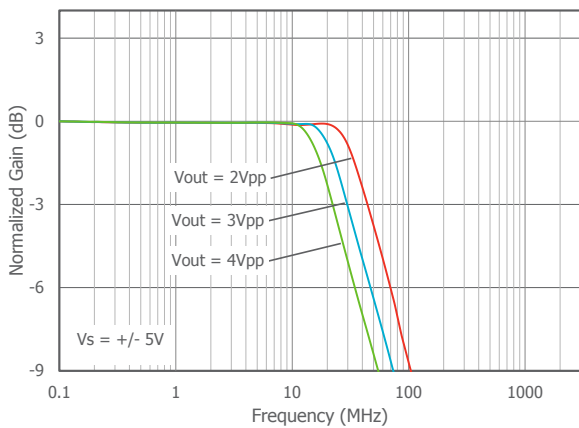
Freq. Resp. vs CL



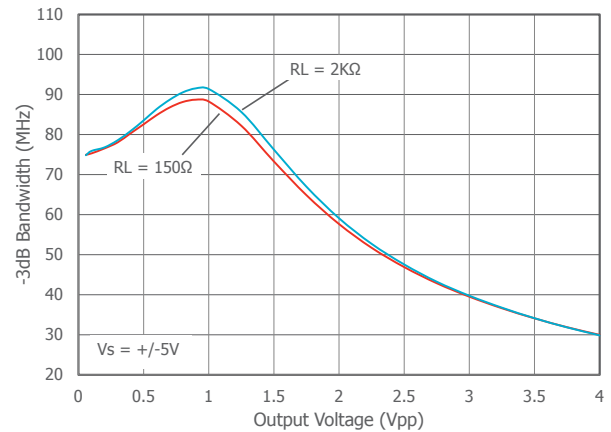
Freq. Resp. vs RL



Large Signal Freq. Resp.



-3dB BW vs Output Voltage

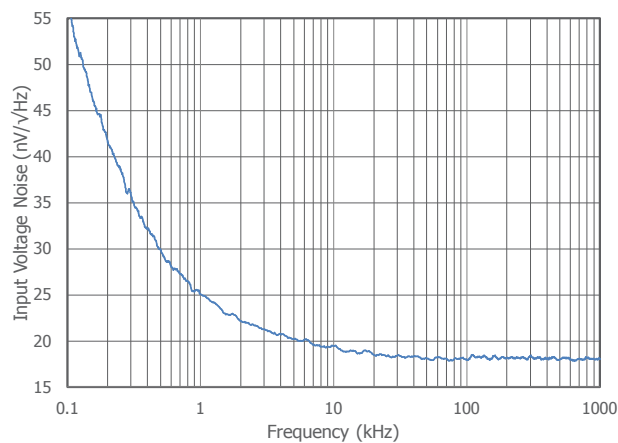




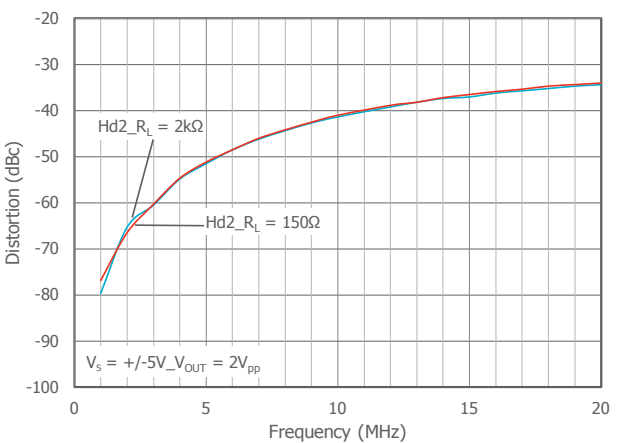
Typical Performance Characteristics

TA = 25°C, VS = ±5V, RL = 2kΩ to GND, AV=+2, RF=1.5kΩ ; unless otherwise noted.

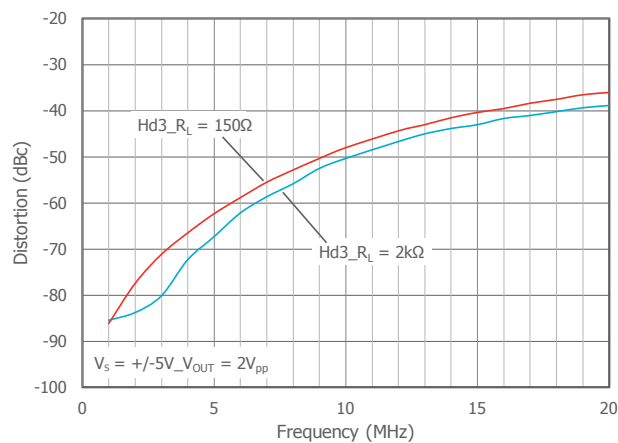
Input Voltage Noise vs Freq.



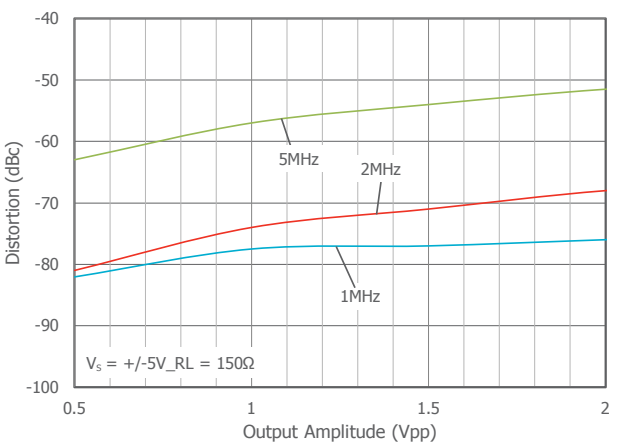
2nd Harmonic Distortion Vs RL over Freq.



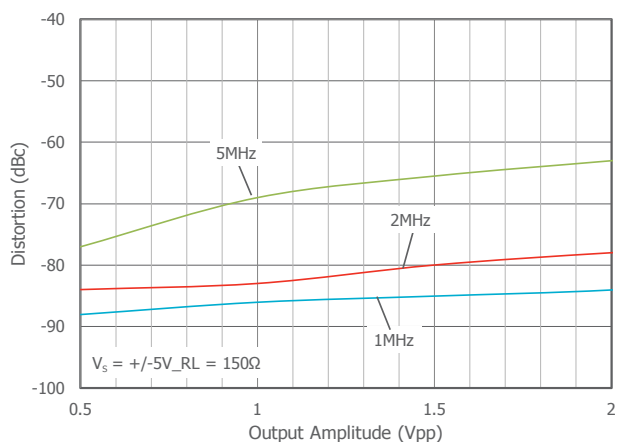
3rd Harmonic Distortion Vs RL over Freq.



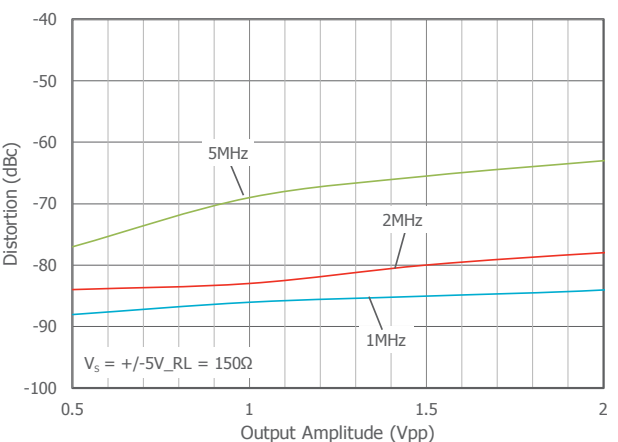
2nd Harmonic Distortion Vs Vo over Freq.



3rd Harmonic Distortion Vs Vo over Freq.



Non-Inverting Small Signal Pulse Response

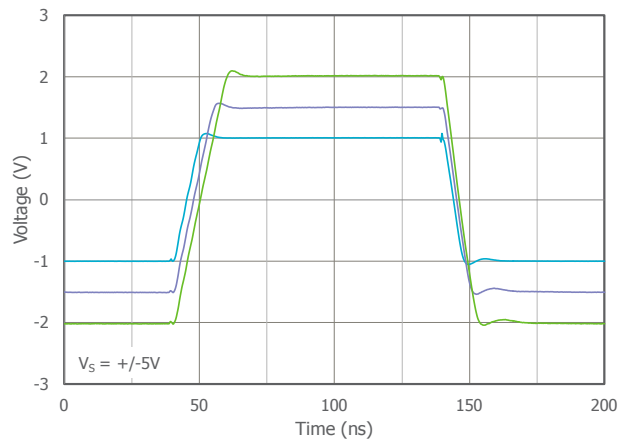




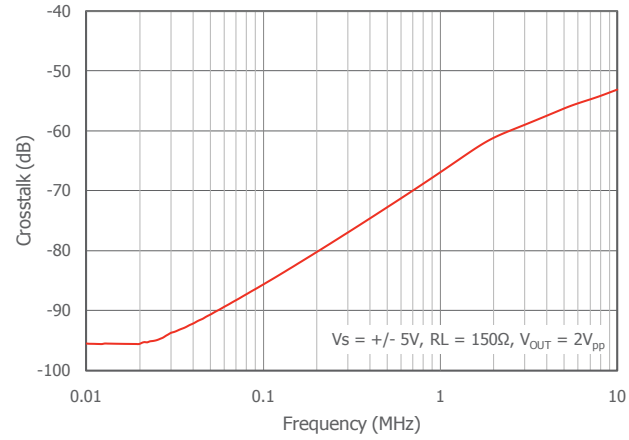
Typical Performance Characteristics

TA = 25°C, VS = ±5V, RL = 2kΩ to GND, AV=+2, RF=1.5kΩ ; unless otherwise noted.

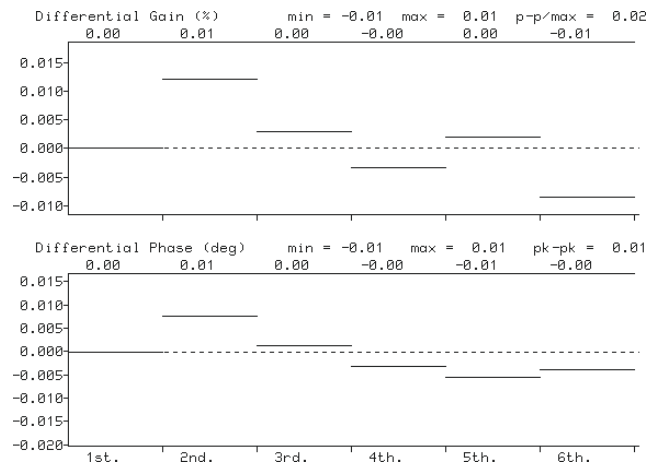
Non-Inverting Large Signal Pulse Response



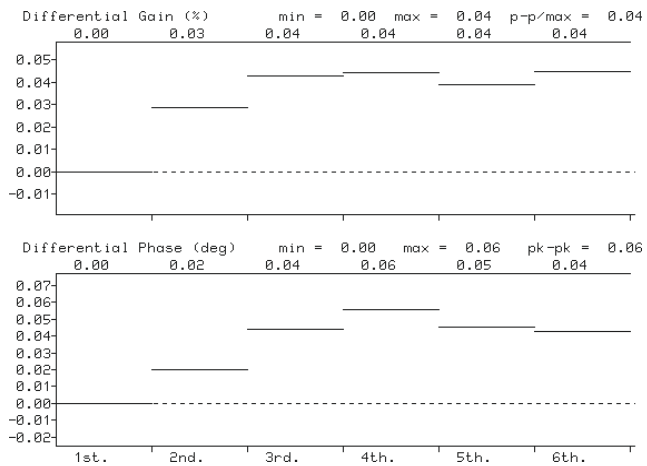
Crosstalk vs Frequency (XR8052)



Differential Gain & Phase_DC Coupled



Differential Gain & Phase_AC Coupled



XR8051, XR8052, XR8054 Low Cost, High Speed Rail-to-Rail Amplifiers Rev 1A



Application Information

General Description

The XR8051, XR8052, and XR8054 are single supply, general purpose, voltage-feedback amplifiers fabricated on a complementary bipolar process using a patent pending topography. They feature a rail-to-rail output stage and is unity gain stable.

The common mode input range extends to 300mV below ground and to 0.9V below V_S . Exceeding these values will not cause phase reversal. However, if the input voltage exceeds the rails by more than 0.5V, the input ESD devices will begin to conduct. The output will stay at the rail during this overdrive condition.

The output stage is short circuit protected and offers "soft" saturation protection that improves recovery time.

Figures 1, 2, and 3 illustrate typical circuit configurations for non-inverting, inverting, and unity gain topologies for dual supply applications. They show the recommended bypass capacitor values and overall closed loop gain equations. Figure 4 shows the typical non-inverting gain circuit for single supply applications.

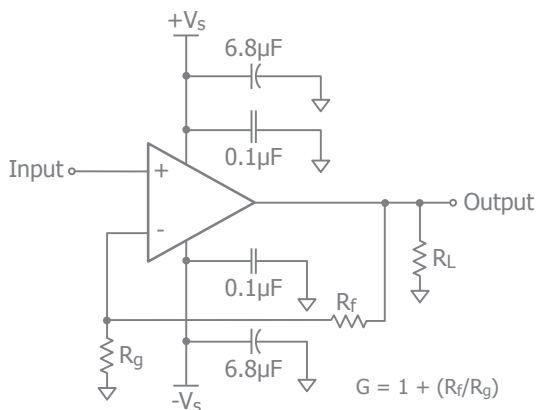


Figure 1. Typical Non-Inverting Gain Circuit

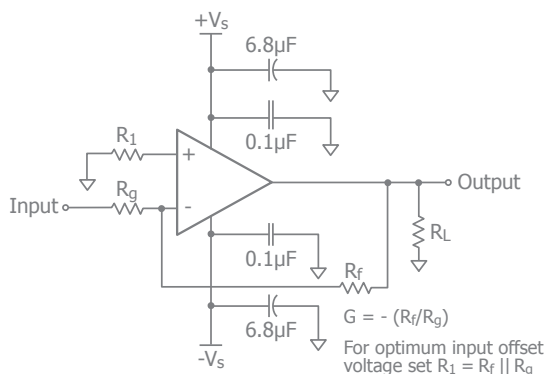


Figure 2. Typical Inverting Gain Circuit

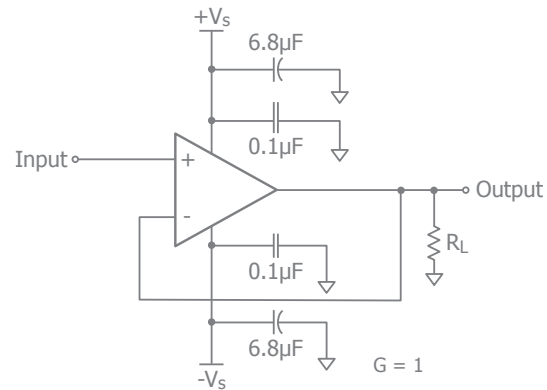


Figure 3. Unity Gain Circuit

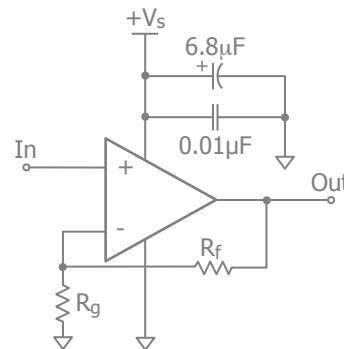


Figure 4. Single Supply Non-Inverting Gain Circuit

Overdrive Recovery

For an amplifier, an overdrive condition occurs when the output and/or input ranges are exceeded. The recovery time varies based on whether the input or output is overdriven and by how much the ranges are exceeded. The XR8051, XR8052, and XR8054 will typically recover in less than 20ns from an overdrive condition. Figure 5 shows the XR8052 in an overdriven condition.

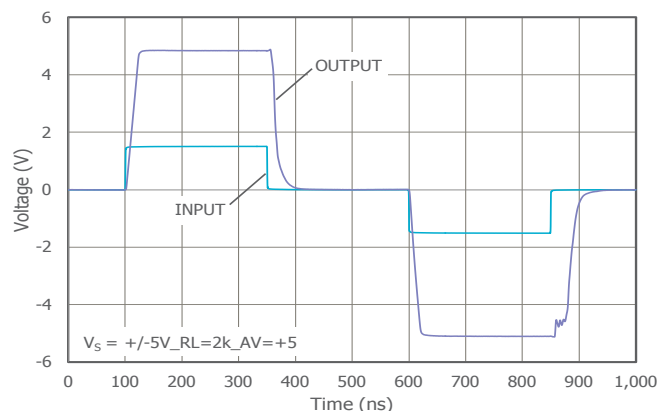


Figure 5: Overdrive Recovery



Power Dissipation

Power dissipation should not be a factor when operating under the stated 2kΩ load condition. However, applications with low impedance, DC coupled loads should be analyzed to ensure that maximum allowed junction temperature is not exceeded. Guidelines listed below can be used to verify that the particular application will not cause the device to operate beyond its intended operating range.

Maximum power levels are set by the absolute maximum junction rating of 170°C. To calculate the junction temperature, the package thermal resistance value Θ_{JA} (Θ_{JA}) is used along with the total die power dissipation.

$$T_{\text{Junction}} = T_{\text{Ambient}} + (\Theta_{JA} \times P_D)$$

Where T_{Ambient} is the temperature of the working environment.

In order to determine P_D , the power dissipated in the load needs to be subtracted from the total power delivered by the supplies.

$$P_D = P_{\text{supply}} - P_{\text{load}}$$

Supply power is calculated by the standard power equation.

$$P_{\text{supply}} = V_{\text{supply}} \times I_{\text{RMS supply}}$$

$$V_{\text{supply}} = V_{S+} - V_{S-}$$

Power delivered to a purely resistive load is:

$$P_{\text{load}} = ((V_{\text{LOAD}})_{\text{RMS}}^2) / R_{\text{load eff}}$$

The effective load resistor ($R_{\text{load eff}}$) will need to include the effect of the feedback network. For instance,

$R_{\text{load eff}}$ in Figure 3 would be calculated as:

$$R_L \parallel (R_f + R_g)$$

These measurements are basic and are relatively easy to perform with standard lab equipment. For design purposes however, prior knowledge of actual signal levels and load impedance is needed to determine the dissipated power. Here, P_D can be found from

$$P_D = P_{\text{Quiescent}} + P_{\text{Dynamic}} - P_{\text{Load}}$$

Quiescent power can be derived from the specified I_S values along with known supply voltage, V_{Supply} . Load power can be calculated as above with the desired signal

amplitudes using:

$$(V_{\text{LOAD}})_{\text{RMS}} = V_{\text{PEAK}} / \sqrt{2}$$

$$(I_{\text{LOAD}})_{\text{RMS}} = (V_{\text{LOAD}})_{\text{RMS}} / R_{\text{load eff}}$$

The dynamic power is focused primarily within the output stage driving the load. This value can be calculated as:

$$P_{\text{DYNAMIC}} = (V_{S+} - V_{\text{LOAD}})_{\text{RMS}} \times (I_{\text{LOAD}})_{\text{RMS}}$$

Assuming the load is referenced in the middle of the power rails or $V_{\text{supply}}/2$.

The XR8051 is short circuit protected. However, this may not guarantee that the maximum junction temperature (+170°C) is not exceeded under all conditions. Figure 6 shows the maximum safe power dissipation in the package vs. the ambient temperature for the packages available.

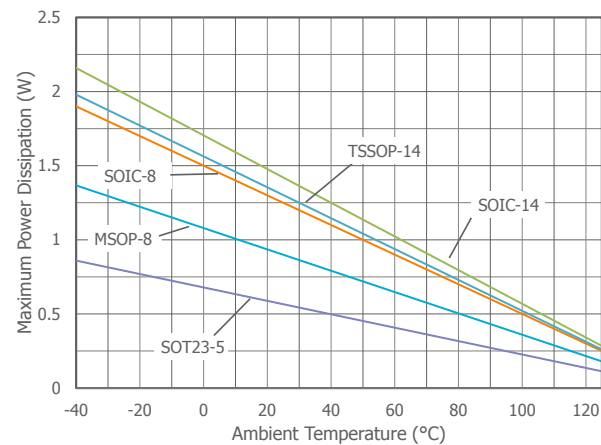


Figure 6. Maximum Power Derating

Driving Capacitive Loads

Increased phase delay at the output due to capacitive loading can cause ringing, peaking in the frequency response, and possible unstable behavior. Use a series resistance, R_S , between the amplifier and the load to help improve stability and settling performance. Refer to Figure 7.

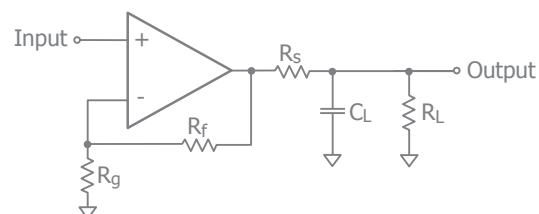


Figure 7. Addition of R_S for Driving Capacitive Loads



Table 1 provides the recommended R_S for various capacitive loads. The recommended R_S values result in approximately <1dB peaking in the frequency response.

CL (Pf)	R_S (Ω)	-3db BW (MHz)
22pF	0	120
47pF	15	80
100pF	15	65
492pF	6.5	40

Table 1: Recommended R_S vs. C_L

For a given load capacitance, adjust R_S to optimize the tradeoff between settling time and bandwidth. In general, reducing R_S will increase bandwidth at the expense of additional overshoot and ringing.

Layout Considerations

General layout and supply bypassing play major roles in high frequency performance. CADEKA has evaluation boards to use as a guide for high frequency layout and as an aid in device testing and characterization. Follow the steps below as a basis for high frequency layout:

- Include 6.8 μ F and 0.1 μ F ceramic capacitors for power supply decoupling
- Place the 6.8 μ F capacitor within 0.75 inches of the power pin
- Place the 0.1 μ F capacitor within 0.1 inches of the power pin
- Remove the ground plane under and around the part, especially near the input and output pins to reduce parasitic capacitance
- Minimize all trace lengths to reduce series inductances

Refer to the evaluation board layouts below for more information.

Evaluation Board Information

The following evaluation boards are available to aid in the testing and layout of these devices:

Evaluation Board	Products
CEB002	XR8051 in SOT23
CEB003	XR8051 in SOIC

Evaluation Board	Products
CEB006	XR8052 in SOIC
CEB010	XR8052 in MSOP
CEB018	XR8054 in SOIC

Evaluation Board Schematics

Evaluation board schematics and layouts are shown in Figures 10-18. These evaluation boards are built for dual-supply operation. Follow these steps to use the board in a single-supply application:

1. Short -Vs to ground.
2. Use C3 and C4, if the -Vs pin of the amplifier is not directly connected to the ground plane.

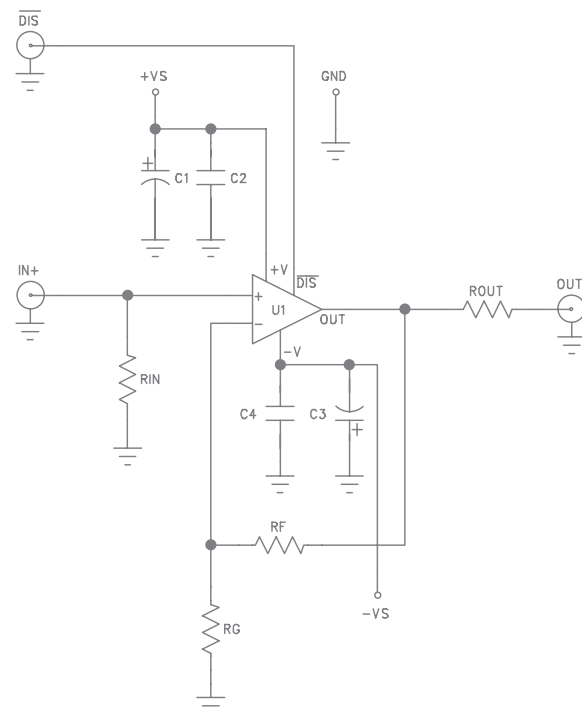


Figure 8. CEB002 & CEB003 Schematic

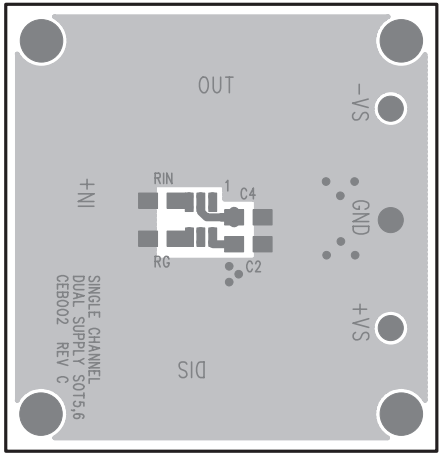


Figure 9. CEB002 Top View

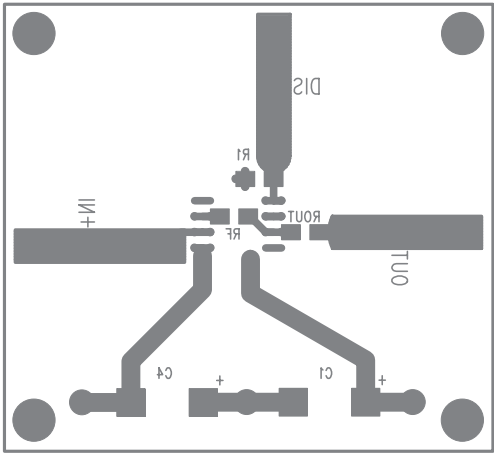


Figure 12. CEB003 Bottom View

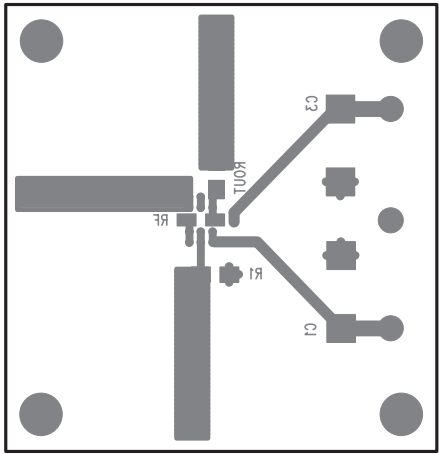


Figure 10. CEB002 Bottom View

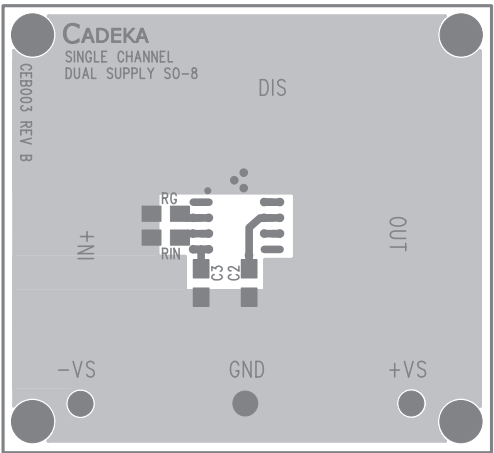


Figure 11. CEB003 Top View

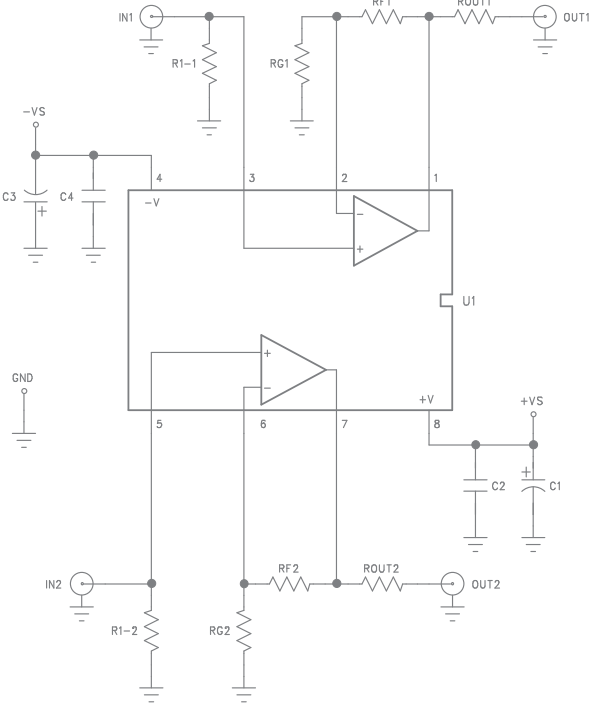


Figure 13. CEB006 & CEB010 Schematic

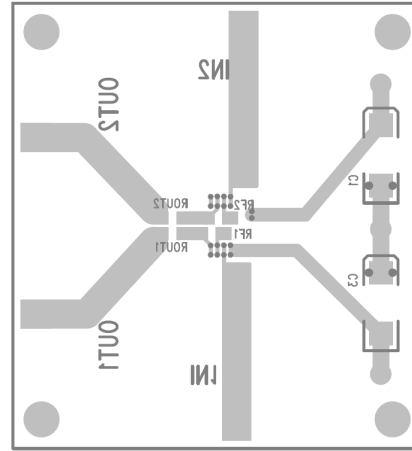


Figure 17. CEB010 Bottom View

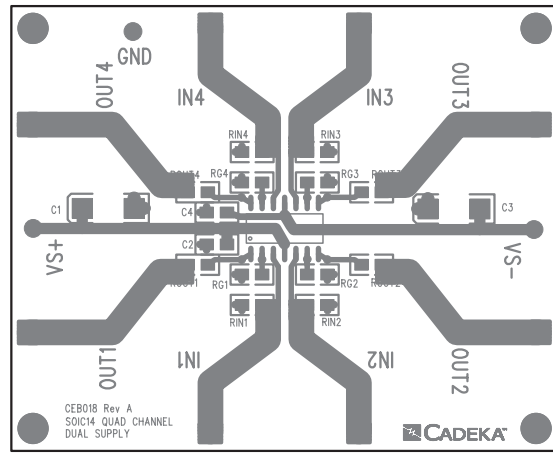


Figure 19. CEB018 Bottom View

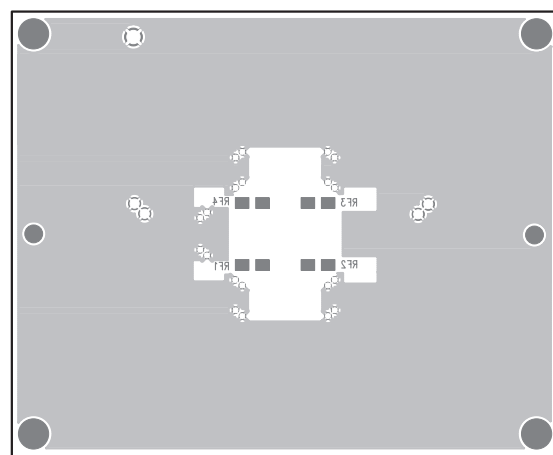
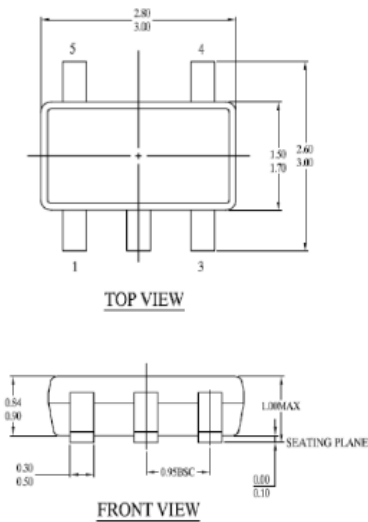


Figure 20. CEB018 Bottom View

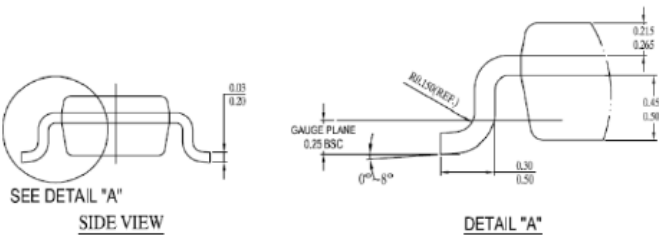


Mechanical Dimensions

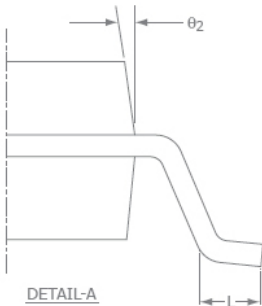
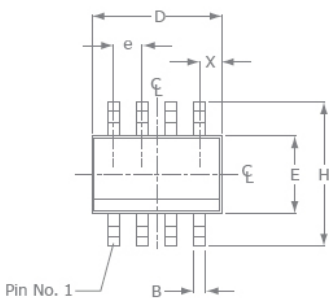
TSOT-5 Package



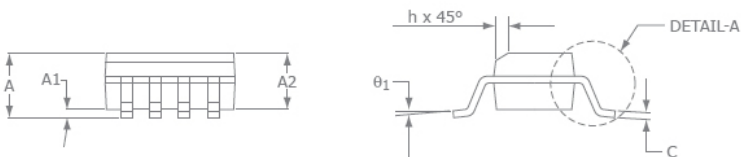
- NOTE:
- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
 - 2. PACKAGE LENGTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION
 - 3. PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 - 4. LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.10 MILLIMETERS MAX.
 - 5. DRAWING CONFORMS TO JEDEC MO-193, VARIATION AA.
 - 6. DRAWING IS NOT TO SCALE.



SOIC-8



SOIC-8		
SYMBOL	MIN	MAX
A1	0.10	0.25
B	0.36	0.48
C	0.19	0.25
D	4.80	4.98
E	3.81	3.99
e	1.27 BSC	
H	5.80	6.20
h	0.25	0.5
L	0.41	1.27
A	1.37	1.73
theta_1	0°	8°
X	0.55 ref	
theta_2	7° BSC	

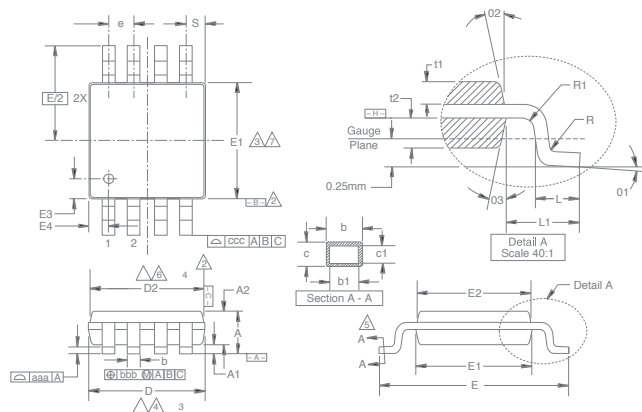


- NOTE:
- 1. All dimensions are in millimeters.
 - 2. Lead coplanarity should be 0 to 0.1mm (0.004") max.
 - 3. Package surface finishing: VDI 24~27
 - 4. All dimension excluding mold flashes.
 - 5. The lead width, B to be determined at 0.1905mm from the lead tip.



Mechanical Dimensions continued

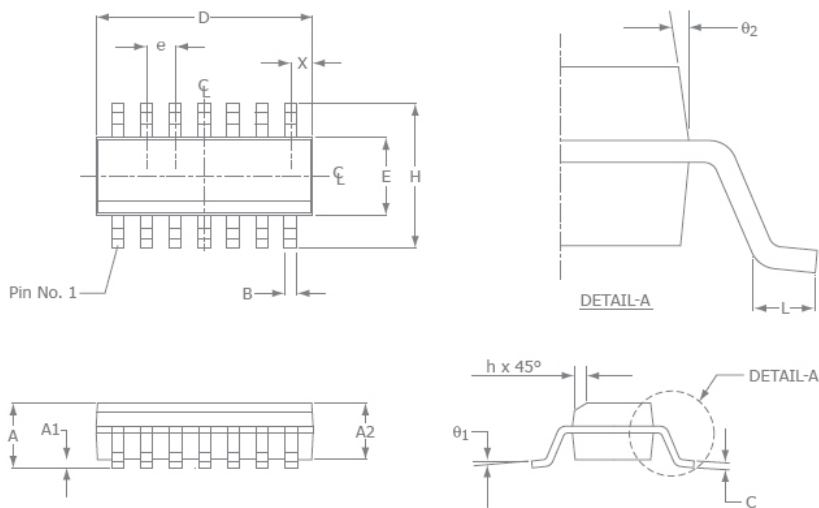
MSOP-8



NOTE:
1 All dimensions are in millimeters (angle in degrees), unless otherwise specified.
△ Datums $\square B$ and $\square C$ to be determined at datum plane $\square H$.
△ Dimensions "D" and "E1" are to be determined at datum $\square H$.
△ Dimensions "D2" and "E2" are for top package and dimensions "D" and "E1" are for bottom package.
△ Cross sections A – A to be determined at 0.13 to 0.25mm from the leadtip.
△ Dimension "D" and "D2" does not include mold flash, protrusion or gate burrs.
△ Dimension "E1" and "E2" does not include interlead flash or protrusion.

Symbol	Min	Max
A	1.10	—
A1	0.10	±0.05
A2	0.86	±0.08
D	3.00	±0.10
D2	2.95	±0.10
E	4.90	±0.15
E1	3.00	±0.10
E2	2.95	±0.10
E3	0.51	±0.13
E4	0.51	±0.13
R	0.15	+0.15/-0.06
R1	0.15	+0.15/-0.06
t1	0.31	±0.08
t2	0.41	±0.08
b	0.33	+0.07/-0.08
b1	0.30	±0.05
c	0.18	±0.05
c1	0.15	+0.03/-0.02
01	3.0°	±3.0°
02	12.0°	±3.0°
03	12.0°	±3.0°
L	0.55	±0.15
L1	0.95 BSC	—
aaa	0.10	—
bbb	0.08	—
ccc	0.25	—
e	0.65 BSC	—
S	0.525 BSC	—

SOIC-14 Package



SOIC-14		
SYMBOL	MIN	MAX
A1	0.10	0.25
B	0.36	0.48
C	0.19	0.25
D	8.56	8.74
E	3.84	3.99
e	1.27 BSC	
H	5.80	6.20
h	0.25	0.5
L	0.41	1.27
A	1.37	1.73
θ ₁	0°	8°
X	0.51 ref	
θ ₂	7° BSC	

NOTE:
1. All dimensions are in millimeters.
2. Lead coplanarity should be 0 to 0.1mm (0.004") ma
3. Package surface finishing: VDI 24~27
4. All dimension excluding mold flashes.
5. The lead width, B to be determined at 0.1905mm from the lead tip.

For Further Assistance:

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